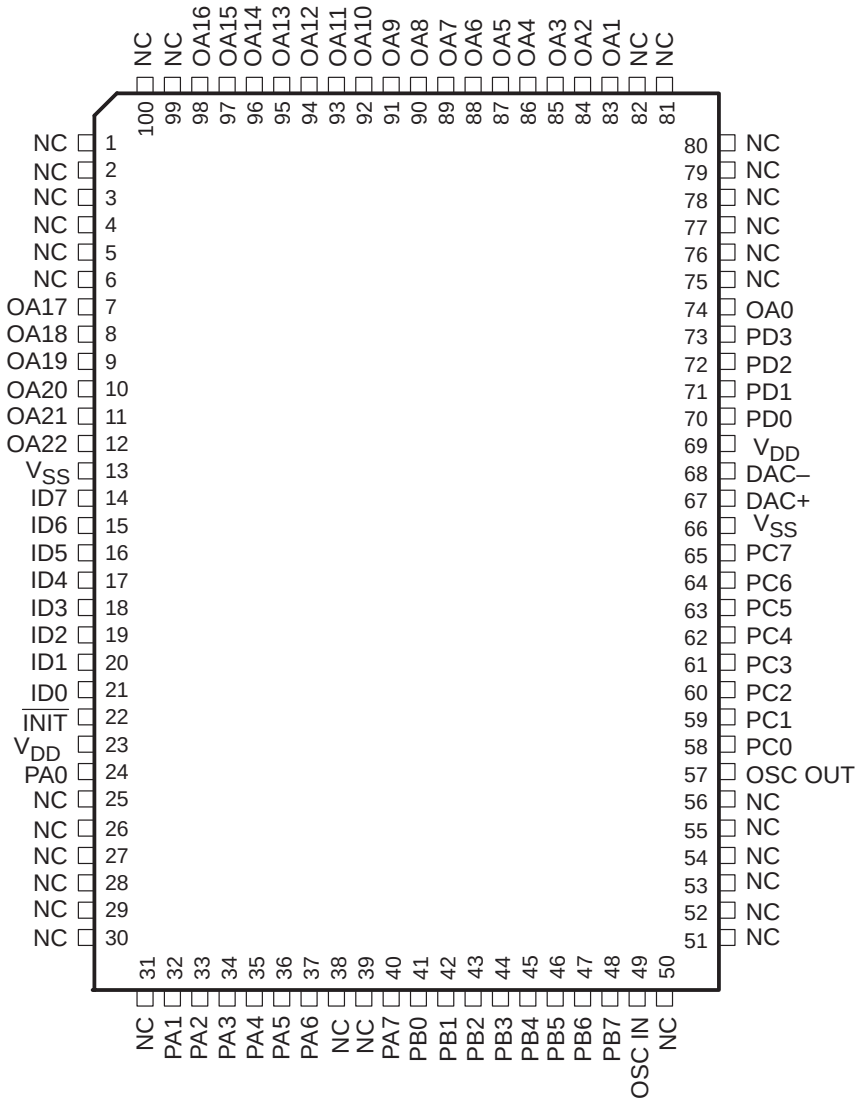
- **Interface to External ROM/EPROM (Up to 8 MBytes)**
- **8-Bit Microprocessor with 61 instructions**
- **32 Twelve-Bit Words and 992 Bytes of RAM**
- **4K Internal ROM**
- **3.3V to 6.5V CMOS Technology for Low Power Dissipation**
- **28 Software-Configurable I/O Lines**
- **10-kHz or 8-kHz Speech Sample Rate**

description

The MSP50C30 combines an 8-bit microprocessor, two speech synthesizers, ROM, RAM, and I/O in a low-cost single-chip system. The architecture uses the same arithmetic logic unit (ALU) for the two synthesizers and the microprocessor, thus reducing chip area and cost and enabling the microprocessor to do a multiply operation in 0.8 μs. The MSP50C30 features two independent channels of linear predictive coding (LPC), which synthesize high-quality speech at a low data rate. Pulse-code modulation (PCM) can produce music or sound effects. For more information, see the MSP50C30 User's Guide (TI literature number SPSU012).

PJM PACKAGE
(TOP VIEW)



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

absolute maximum ratings over operating free-air temperature range†

Supply voltage range, V_{DD} (see Note 1) . . . . . –0.3 V to 8 V
Supply current, I_{DD} or I_{SS} (see Note 2) . . . . . 100 mA
Input voltage range, V_I (see Note 1) . . . . . –0.3 V to V_{DD} + 0.3 V
Output voltage range, V_O (see Note 1) . . . . . –0.3 V to V_{DD} + 0.3 V
Storage temperature range . . . . . –30°C to 125°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to ground.
2. The total supply current includes the current out of all the I/O terminals and DAC terminals as well as the operating current of the device.

recommended operating conditions (MSP50C30)

			MIN	MAX	UNIT
V_{DD}	Supply voltage†		3.3	6.5	V
V_{IH}	High-level input voltage	V_{DD} = 3.3 V	2.5	3.3	V
		V_{DD} = 5 V	3.8	5	
		V_{DD} = 6 V	4.5	6	
V_{IL}	Low-level input voltage	V_{DD} = 3.3 V	0	0.65	V
		V_{DD} = 5 V	0	1	
		V_{DD} = 6 V	0	1.3	
T_A	Operating free-air temperature	Device functionality	0	70	°C
Rspeaker	Minimum speaker impedance	Direct speaker drive using 2 pin push-pull DAC option	32		Ω

† Unless otherwise noted, all voltages are with respect to V_{SS}.

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{T+}	Positive-going threshold voltage (INIT)	V_{DD} = 3.5 V		2		V
		V_{DD} = 6 V		3.4		
V_{T-}	Negative-going threshold voltage (INIT)	V_{DD} = 3.5 V		1.6		V
		V_{DD} = 6 V		2.3		
V_{hys}	Hysteresis ($V_{T+} - V_{T-}$) (INIT)	V_{DD} = 3.5 V		0.4		V
		V_{DD} = 6 V		1.1		
I_{lkg}	Input leakage current (except for OSC IN)				2	µA
$I_{standby}$	Standby current ($\overline{INIT}$ low, SETOFF)				10	µA
I_{DD}†	Supply current	V_{DD} = 3.3 V,		2.1		mA
		V_{DD} = 5 V,		3.1		
		V_{DD} = 6 V,		4.5		
I_{OH}	High-level output current (PA, PB)	V_{DD} = 3.3 V, V_{OH} = 2.75 V	–4	–12		mA
		V_{DD} = 5 V, V_{OH} = 4.5 V	–5	–14		
		V_{DD} = 6 V, V_{OH} = 5.5 V	–6	–15		
		V_{DD} = 3.3 V, V_{OH} = 2.2 V	–8	–20		mA
		V_{DD} = 5 V, V_{OH} = 3.33 V	–14	–40		
		V_{DD} = 6 V, V_{OH} = 4 V	–20	–51		
I_{OL}	Low-level output current (PA, PB)	V_{DD} = 3.3 V, V_{OL} = 0.5 V	5	9		mA
		V_{DD} = 5 V, V_{OL} = 0.5 V	5	9		
		V_{DD} = 6 V, V_{OL} = 0.5 V	5	9		
		V_{DD} = 3.3 V, V_{OL} = 1.1 V	10	19		mA
		V_{DD} = 5 V, V_{OL} = 1.67 V	20	29		
		V_{DD} = 6 V, V_{OL} = 2 V	25	35		
I_{OH}	High-level output current (D/A)	V_{DD} = 3.3 V, V_{OH} = 2.75 V	–30	–50		mA
		V_{DD} = 5 V, V_{OH} = 4.5 V	–35	–60		
		V_{DD} = 6 V, V_{OH} = 5.5 V	–40	–65		
		V_{DD} = 3.3 V, V_{OH} = 2.3 V	–50	–90		mA
		V_{DD} = 5 V, V_{OH} = 4 V	–90	–140		
		V_{DD} = 6 V, V_{OH} = 5 V	–100	–150		
I_{OL}	Low-level output current (D/A)	V_{DD} = 3.3 V, V_{OL} = 0.5 V	50	80		mA
		V_{DD} = 5 V, V_{OL} = 0.5 V	70	90		
		V_{DD} = 6 V, V_{OL} = 0.5 V	80	110		
		V_{DD} = 3.3 V, V_{OL} = 1 V	100	140		mA
		V_{DD} = 5 V, V_{OL} = 1 V	140			
		V_{DD} = 6 V, V_{OL} = 1 V	150			
	Pullup resistance	Resistors selected by software and connected between terminal and V_{DD}	10	20	50	kΩ
$f_{osc(low)}$	Oscillator frequency‡	V_{DD} = 5 V, T_A = 25°C, Target frequency = 15.36 MHz	14.89	15.36	15.86	MHz
$f_{osc(high)}$	Oscillator frequency‡	V_{DD} = 5 V, T_A = 25°C, Target frequency = 19.2 MHz	18.62	19.2	19.7	MHz

† Operating current assumes all inputs are tied to either V_{SS} or V_{DD} with no input currents due to programmed pullup resistors. The DAC output and other outputs are open circuited.

‡ The frequency of the internal clock has a temperature coefficient of approximately –0.2 %/°C and a V_{DD} coefficient of approximately ±1%/V.

switching characteristics

PARAMETER			TEST CONDITIONS			MIN	NOM	MAX	UNIT
t_r	Rise time	PA, PB, PC, PD, D/A	V_{DD} = 3.3 V,	C_L = 100 pF,	10% to 90%		50		ns
		OA	V_{DD} = 3.3 V,	C_L = 50 pF,	10% to 90%		50		
t_f	Fall time	PA, PB, PC, PD, D/A	V_{DD} = 3.3 V,	C_L = 100 pF,	10% to 90%		50		ns
		OA	V_{DD} = 3.3 V,	C_L = 50 pF,	10% to 90%		50		

timing requirements

			MIN	MAX	UNIT
Initialization					
t_{INIT}	$\overline{INIT}$ pulsed low while the MSP50x3x has power applied (see Figure 1)		1		µs
Wakeup					
$t_{su(wakeup)}$	Setup time prior to wakeup terminal negative transition (see Figure 2)		1		µs
External Interrupt					
$t_{su(interrupt)}$	Setup time prior to B1 terminal negative transition (see Figure 3)	f_{clock} = 15.36 MHz	1		µs
		f_{clock} = 19.2 MHz	1.5		
Writing (Slave Mode)					
$t_{su1(B1)}$	Setup time, B1 low before B0 goes low (see Figure 4)		20		ns
$t_{su(d)}$	Setup time, data valid before B0 goes high (see Figure 4)		100		ns
$t_{h1(B1)}$	Hold time, B1 low after B0 goes high (see Figure 4)		20		ns
$t_{h(d)}$	Hold time, data valid after B0 goes high (see Figure 4)		30		ns
t_w	Pulse duration, B0 low (see Figure 4)		100		ns
t_r	Rise time, B0 (see Figure 4)			50	ns
t_f	Fall time, B0 (see Figure 4)			50	ns
Reading (Slave Mode)					
$t_{su2(B1)}$	Setup time, B1 before B0 goes low (see Figure 5)		20		ns
$t_{h2(B1)}$	Hold time, B1 after B0 goes high (see Figure 5)		20		ns
t_{dis}	Output disable time, data valid after B0 goes high (see Figure 5)		0	30	ns
t_w	Pulse duration, B0 low (see Figure 5)		100		ns
t_r	Rise time, B0 (see Figure 5)			50	ns
t_f	Fall time, B0 (see Figure 5)			50	ns
t_d	Delay time for B0 low to data valid (see Figure 5)			50	ns
External ROM					
$t_{a(ROM)}$	ROM access time			400	ns

PARAMETER MEASUREMENT INFORMATION

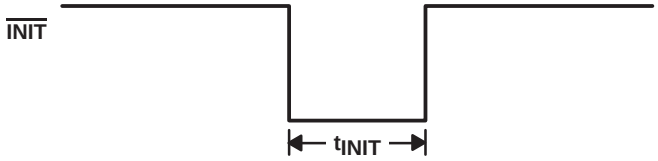


Figure 1. Initialization Timing Diagram

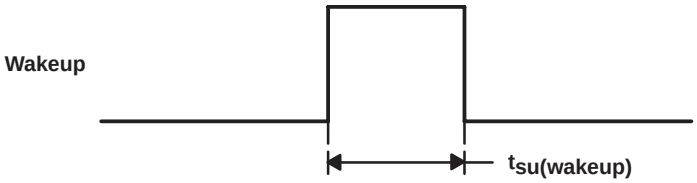


Figure 2. Wakeup Terminal Setup Timing Diagram

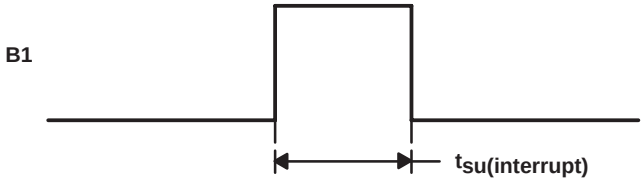


Figure 3. External Interrupt Terminal Setup Timing Diagram

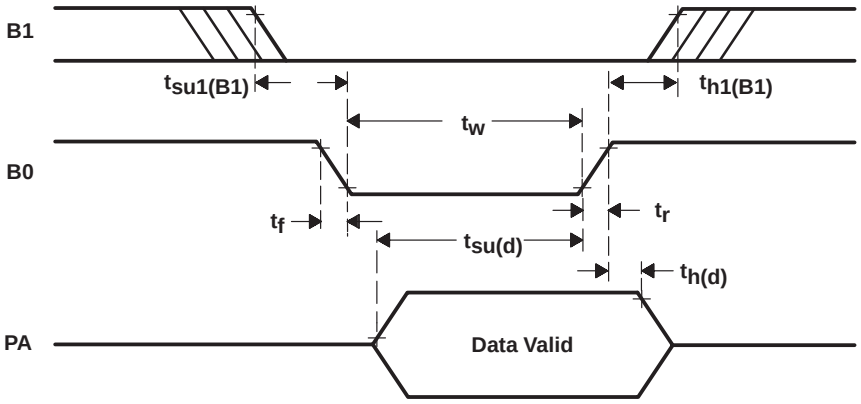


Figure 4. Write Timing Diagram (Slave Mode)

PARAMETER MEASUREMENT INFORMATION

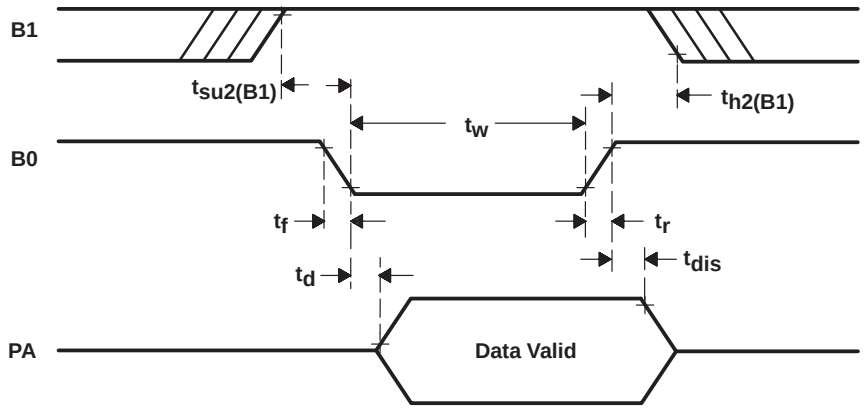
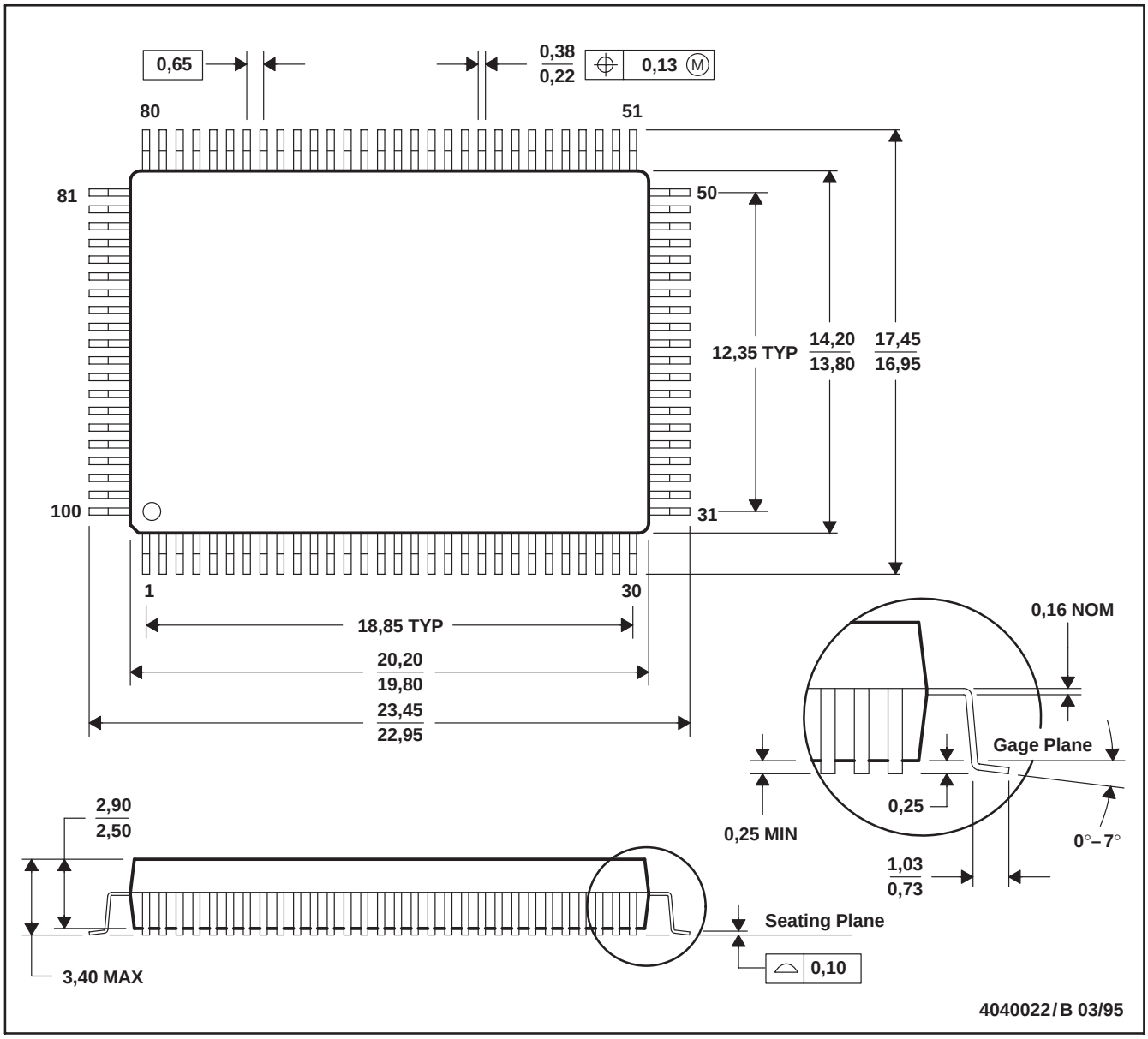


Figure 5. Read Timing Diagram (Slave Mode)

MECHANICAL DATA

PJM (R-PQFP-G100) **PLASTIC QUAD FLATPACK**



NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Falls within JEDEC MS-022

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgment, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Customers are responsible for their applications using TI components.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.